

N-channel 60 V 2.2 mΩ standard level MOSFET in I2PAK

Rev. 02 — 19 April 2011

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in a I2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
 - sources

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

Suitable for standard level gate drive

1.4 Quick reference data

Table 1.	Quick reference data
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	dulon reference dulu						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	60	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V};$ see <u>Figure 1</u>	[1]	-	-	120	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see Figure 2		-	-	338	W
Tj	junction temperature			-55	-	175	°C
Static cha	racteristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 12</u>	[2]	-	1.8	2.2	mΩ
		$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \\ T_{j} = 100 \ ^{\circ}\text{C}; \text{ see } \underline{\text{Figure 12}}; \\ \text{see } \underline{\text{Figure 13}} \end{array}$		-	3	3.5	mΩ
Dynamic of	characteristics						
Q _{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; \text{ I}_{D} = 75 \text{ A};$		-	32	-	nC
Q _{G(tot)}	total gate charge	$V_{DS} = 30 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 15}$		-	137	-	nC
Avalanche	e ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{array}{l} V_{GS} = 10 \text{ V}; \ T_{j(\text{init})} = 25 \ ^{\circ}\text{C}; \\ I_{D} = 120 \text{ A}; \ V_{sup} \leq 60 \text{ V}; \\ R_{GS} = 50 \ \Omega; \ Unclamped \end{array} $		-	-	913	mJ

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- [1] Continuous current limited by package.
- [2] Measured 3 mm from package.

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbbo76 S

SOT226 (I2PAK)

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
PSMN2R0-60ES	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226

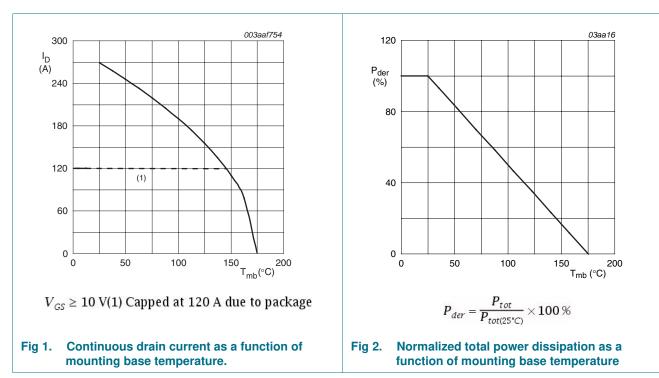
4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

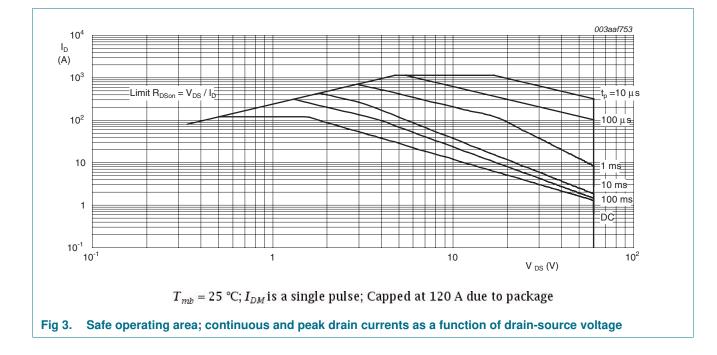
Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	60	V
V _{DGR}	drain-gate voltage	T _j ≥ 25 °C; T _j ≤ 175 °C; R _{GS} = 20 kΩ		-	60	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u>	[1]	-	120	А
		V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	[1]	-	120	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3		-	1135	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	338	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-drai	n diode					
I _S	source current	T _{mb} = 25 °C	<u>[1]</u>	-	120	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	1135	А
Avalanche r	ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 120 A; $V_{sup} \le 60$ V; R_{GS} = 50 Ω ; Unclamped		-	913	mJ

[1] Continuous current limited by package



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5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
-						Unit.
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.22	0.44	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	Vertical in free air	-	60	-	K/W

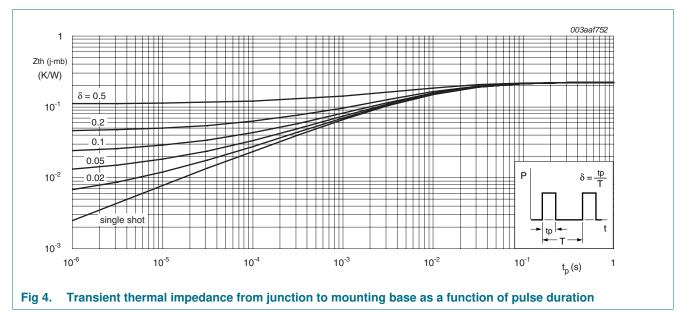


Table 5. Thermal characteristics

6. Characteristics

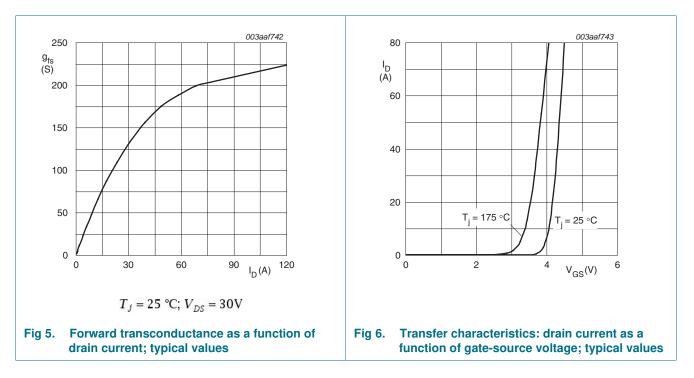
Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static cha	racteristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ\text{C}$	54	-	-	V
	voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	60	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 10</u>	-	-	4.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 10</u>	1	-	-	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; see <u>Figure 11</u> ; see <u>Figure 10</u>	2	3	4	V
I _{DSS}	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.03	10	μA
		$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 12</u>	<u>[1]</u> _	1.8	2.2	mΩ
		V_{GS} = 10 V; I _D = 25 A; T _j = 175 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	4.3	5.1	mΩ
		V_{GS} = 10 V; I _D = 25 A; T _j = 100 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	3	3.5	mΩ
R _G	gate resistance	f = 1 MHz	-	0.9	-	Ω
Dynamic o	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 75 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	137	-	nC
		$I_D = 0 A$; $V_{DS} = 0 V$; $V_{GS} = 10 V$; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	129	-	nC
Q _{GS}	gate-source charge	$I_D = 75 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V}$	-	48	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	$I_D = 75 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	29	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	19	-	nC
Q _{GD}	gate-drain charge		-	32	-	nC
V _{GS(pl)}	gate-source plateau voltage	V _{DS} = 30 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	5.7	-	V
C _{iss}	input capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	9997	-	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 16}{100}$	-	1210	-	pF
C _{rss}	reverse transfer capacitance		-	594	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \ V; \ R_L = 0.4 \ \Omega; \ V_{GS} = 10 \ V;$	-	42	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \ \Omega; \ I_D = 75 \ A$	-	56	-	ns
t _{d(off)}	turn-off delay time		-	115	-	ns
t _f	fall time		-	49	-	ns

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Table 6. Characteristicscontinued	
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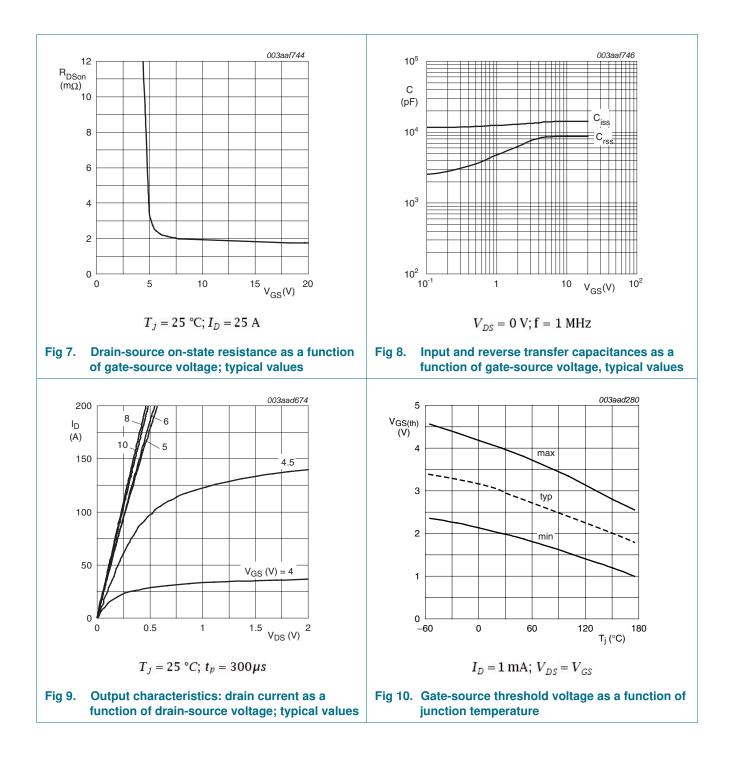
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drain	diode					
V_{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 17</u>	-	0.8	1.2	V
t _{rr}	reverse recovery time	$ I_S = 25 \text{ A}; \ dI_S/dt = -100 \text{ A}/\mu\text{s}; \\ V_{GS} = 0 \text{ V}; \ V_{DS} = 30 \text{ V} $	-	57	-	ns
Q _r	recovered charge	$\label{eq:IS} \begin{array}{l} {\sf I}_{\rm S} = 25 \; {\sf A}; \; {\sf dI}_{\rm S} / {\rm dt} = -100 \; {\sf A} / \mu {\sf s}; \\ {\sf V}_{\rm GS} = 0 \; {\sf V}; \; {\sf V}_{\rm DS} = 30 \; {\sf V} \end{array}$	-	80	-	nC

[1] Measured 3 mm from package.



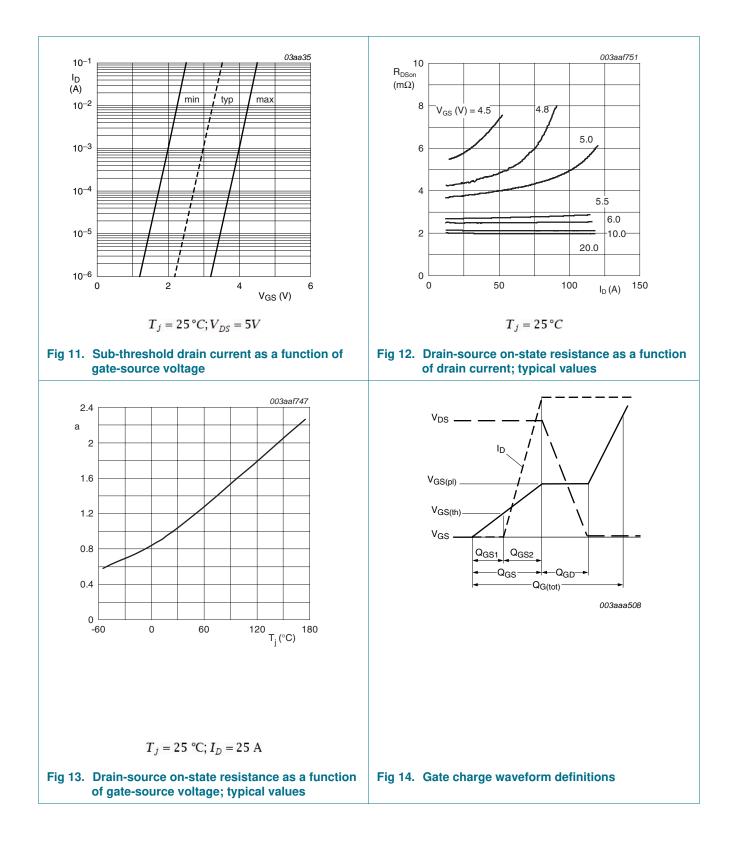
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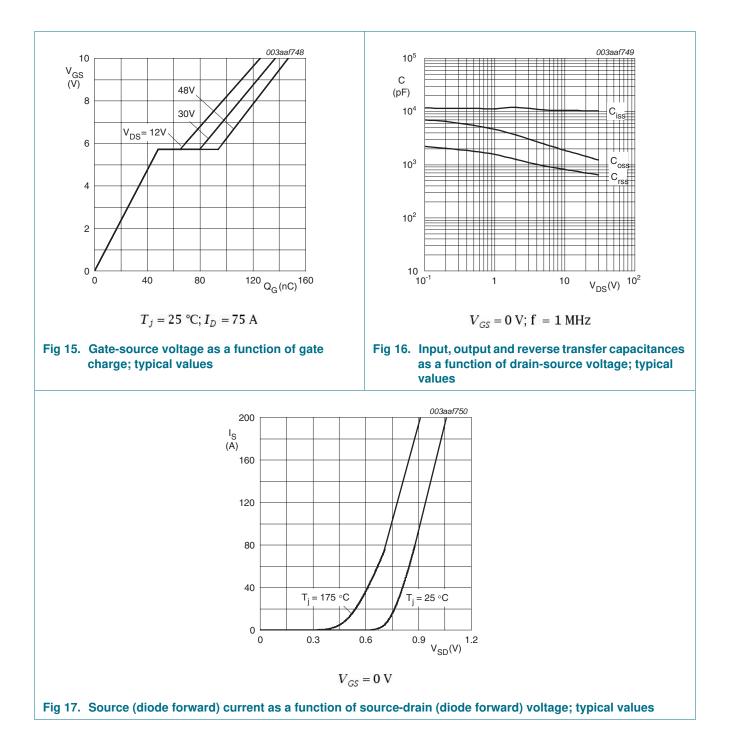
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7. Package outline

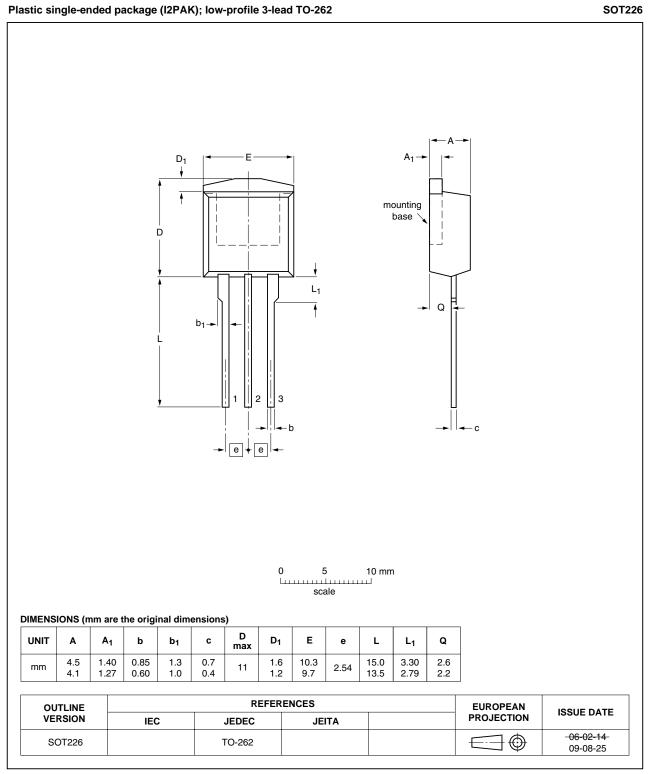


Fig 18. Package outline SOT226 (I2PAK)

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PSMN2R0-60ES

8. Revision history

Table 7. Revision h	nistory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN2R0-60ES v.2	20110419	Product data sheet	-	PSMN2R0-60ES v.1
Modifications:	Status changeVarious chang	d from objective to product. es to content.		
PSMN2R0-60ES v.1	20110117	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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